**Product data sheet** 

## 1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a SOT78 plastic package intended for use in applications requiring sensitive gate, good bidirectional blocking voltage capability, high surge current capability and high thermal cycling performance.

### 2. Features and benefits

- · Good bidirectional blocking voltage capability
- High surge current capability
- · High thermal cycling performance
- Sensitive gate

## 3. Applications

- Ignition circuits
- Motor control
- · Protection circuits
- Voltage regulation

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off- state voltage		-	-	500	V
$V_{RRM}$	repetitive peak reverse voltage		-	-	500	V
I <sub>TSM</sub>	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 10 ms; Fig. 4; Fig. 5	-	-	120	Α
		half sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 8.3 ms	-	-	132	Α
Tj	junction temperature		-	-	125	°C
$I_{T(AV)}$	average on-state current	half sine wave; T <sub>mb</sub> ≤ 109 °C; <u>Fig. 1</u>	-	-	7.5	A
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; $T_{mb} \le 109 ^{\circ}\text{C}$ ; $\overline{\text{Fig. 2}}$ ; $\overline{\text{Fig. 3}}$	-	-	12	A
Static chara	acteristics			'		
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	2	5	mA
Dynamic ch	naracteristics			'	'	

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 335 V; $T_j$ = 125 °C; $R_{GK}$ = 100 Ω; $(V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; Fig. 12	200	1000	-	V/µs

## 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	A <del>- [                                  </del>
2	Α	anode		G sym037
3	G	gate		Symosi
mb	A	mounting base; connected to anode		
			TO-220AB (SOT78)	

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
BT151-500L	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

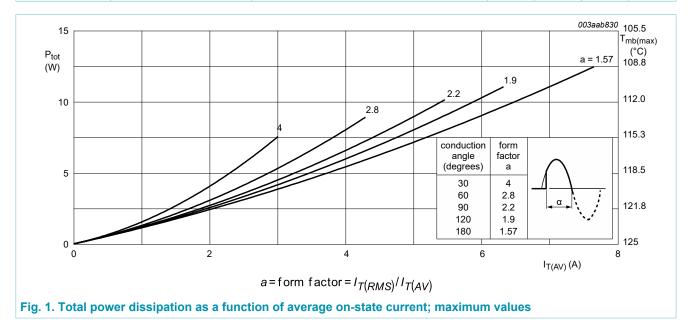
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## 7. Limiting values

### **Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	500	V
$V_{RRM}$	repetitive peak reverse voltage		-	500	V
I <sub>T(AV)</sub>	average on-state current	half sine wave; T <sub>mb</sub> ≤ 109 °C; <u>Fig. 1</u>	-	7.5	Α
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; T <sub>mb</sub> ≤ 109 °C; <u>Fig. 2;</u> <u>Fig. 3</u>	-	12	A
I <sub>TSM</sub>	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 10 ms; Fig. 4; Fig. 5	-	120	Α
		half sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 8.3 ms	-	132	Α
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	72	A²s
dl <sub>T</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 10 mA	-	50	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
$V_{RGM}$	peak reverse gate voltage		-	5	V
$P_{GM}$	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	125	°C



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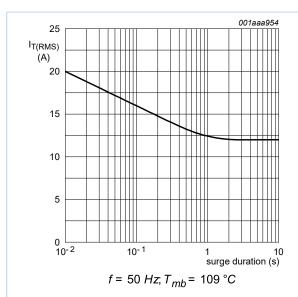


Fig. 2. RMS on-state current as a function of surge duration; maximum values

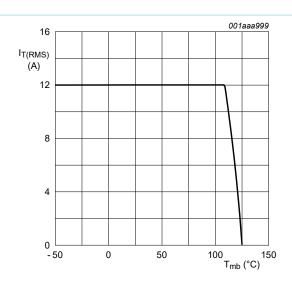


Fig. 3. RMS on-state current as a function of mounting base temperature; maximum values

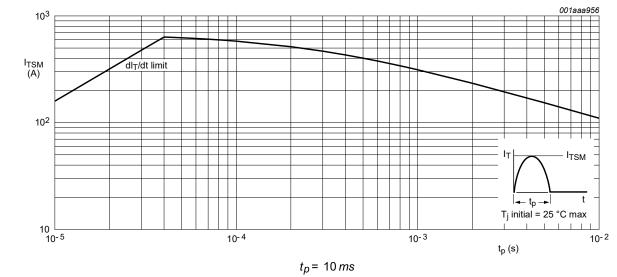


Fig. 4. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values

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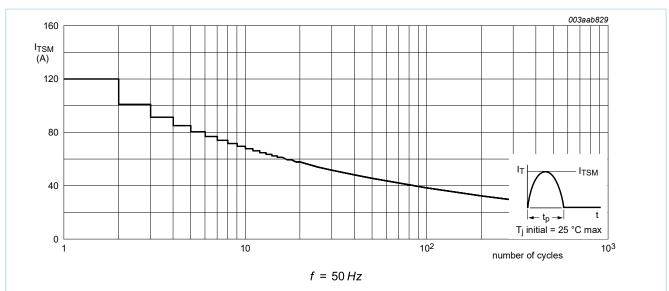


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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### 8. Thermal characteristics

**Table 5. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 6	-	-	1.3	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

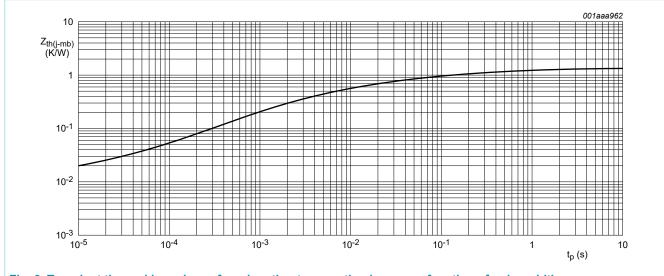


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

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### 9. Characteristics

**Table 6. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					_
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	2	5	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 8$	-	10	40	mA
I <sub>H</sub>	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C}; Fig. 9$	-	7	20	mA
$V_{T}$	on-state voltage	I <sub>T</sub> = 23 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.4	1.75	V
V <sub>GT</sub> gate tr	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.6	1.5	V
		$V_D = 500 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 500 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
I <sub>R</sub>	reverse current	V <sub>R</sub> = 500 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic ch	naracteristics		,			
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 335 V; $T_j$ = 125 °C; $R_{GK}$ = 100 Ω; $(V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; Fig. 12	200	1000	-	V/µs
		$V_{DM}$ = 335 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit; Fig. 12	50	130	-	V/µs
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM}$ = 40 A; $V_D$ = 500 V; $I_G$ = 0.1 A; $dI_G/dt$ = 5 A/µs; $T_j$ = 25 °C	-	2	-	μs
t <sub>q</sub>	commutated turn-off time	$V_{DM}$ = 335 V; $T_j$ = 125 °C; $I_{TM}$ = 20 A; $V_R$ = 25 V; $(dI_T/dt)_M$ = 30 A/µs; $dV_D/dt$ = 50 V/µs; $R_{GK(ext)}$ = 100 $\Omega$ ; $(V_{DM}$ = 67% of $V_{DRM}$ )	-	70	-	μs

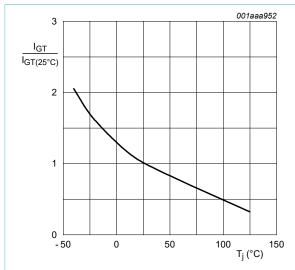


Fig. 7. Normalized gate trigger current as a function of junction temperature

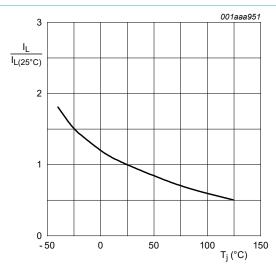


Fig. 8. Normalized latching current as a function of junction temperature

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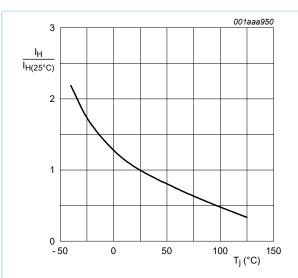
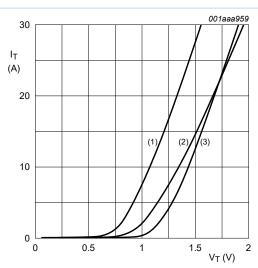


Fig. 9. Normalized holding current as a function of junction temperature



 $V_o$  = 1.06 V;  $R_s$  = 0.0304 Ω (1)  $T_j$  = 125 °C; typical values (2)  $T_j$  = 125 °C; maximum values (3)  $T_j$  = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

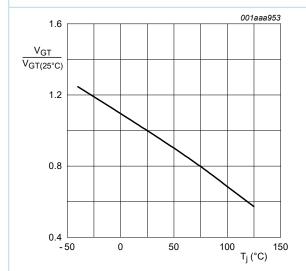
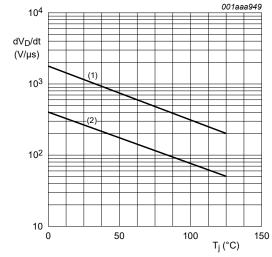


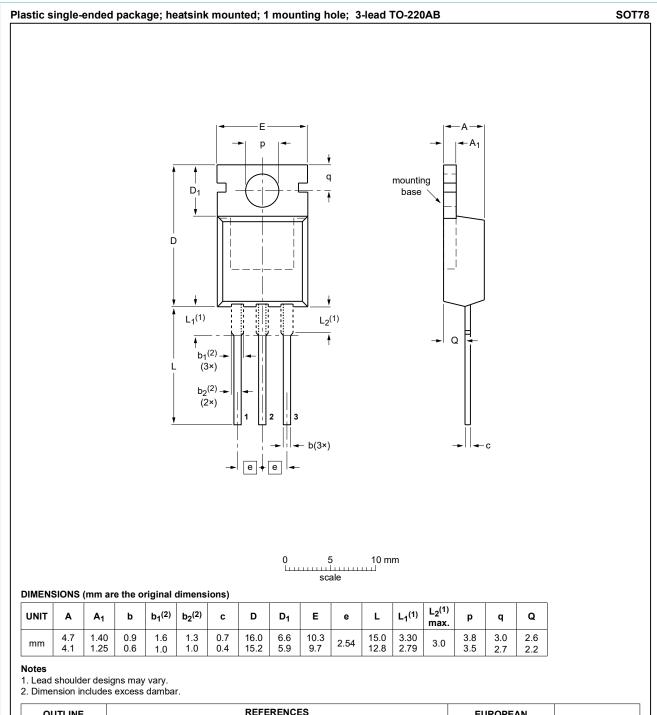
Fig. 11. Normalized gate trigger voltage as a function of junction temperature



(1)  $R_{GK} = 100 \Omega$ ; (2) gate open circuit

Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; minimum values

## 10. Package outline



OUTLINE		REFERENCES			EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46			<del>08-04-23</del> 08-06-13
					- 1	

Fig. 13. Package outline TO-220AB (SOT78)

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## 11. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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